SN74LVC1G79 Single Positive-Edge-Triggered D-Type Flip-Flop

1 Features

- Available in the Texas Instruments NanoFree™ Package
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Supports Down Translation to V_{CC}
- Max t_{pd} of 6 ns at 3.3 V and 50 pF load
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} supports Partial-Power-Down Mode and Back-Drive Protection

2 Applications

- Test and Measurement
- Enterprise Switching
- Telecom Infrastructure
- Personal Electronics
- White Goods

3 Description

The SN74LVC1G79 device is a single positive-edge-triggered D-type flip-flop that is designed for 1.65-V to 5.5-V V_{CC} operation.

When data at the data (D) input meets the setup time requirement, the data is transferred to the Q output on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input can be changed without affecting the level at the output.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

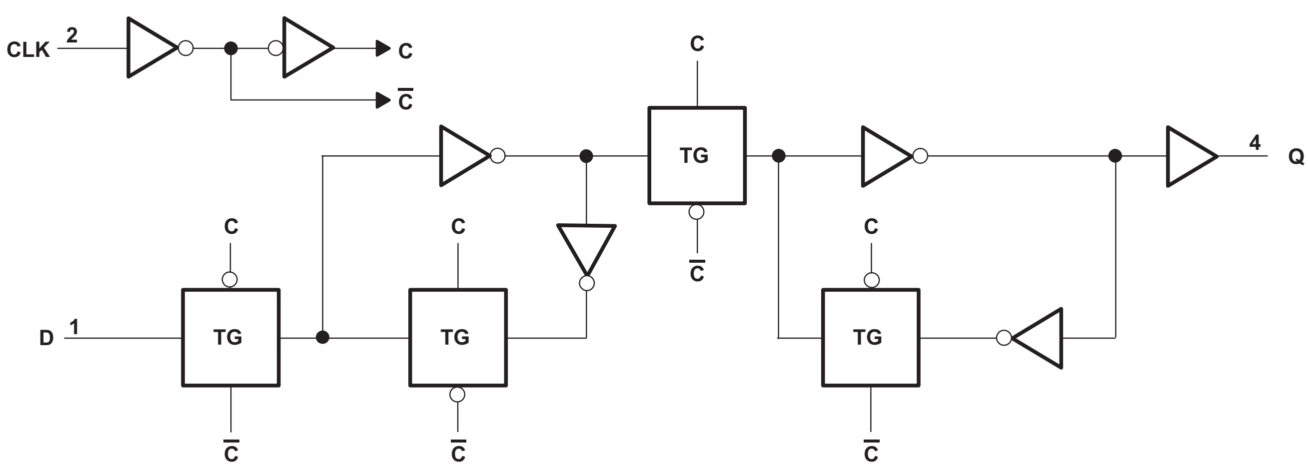
This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs when the device is powered down. This inhibits current backflow into the device which prevents damage to the device.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE
SN74LVC1G79DBV	SOT-23 (5)	2.90 mm × 1.60 mm
SN74LVC1G79DCK	SC70 (5)	2.00 mm × 1.25 mm
SN74LVC1G79DRL	SOT (5)	1.60 mm × 1.20 mm
SN74LVC1G79YZP	DSBGA (5)	1.14 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)



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4 Revision History

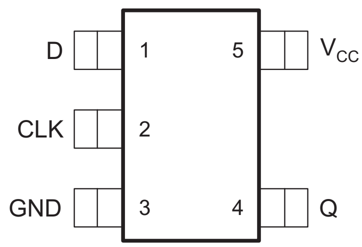
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision T (December 2013) to Revision U	Page
• Added *Device Information* table, *ESD Ratings* table, *Thermal Information* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section	1
• Changed thermal information to align with JEDEC standards.	5

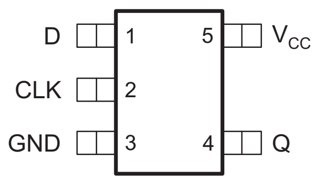
Changes from Revision S (November 2007) to Revision T	Page
• Updated document to new TI data sheet format.	1
• Removed Ordering Information table.	1
• Updated I_{off} in Features.	1
• Updated operating temperature range.	5
• Added ESD warning.	15

5 Pin Configuration and Functions

DBV Package
5-Pin SOT-23
Top View

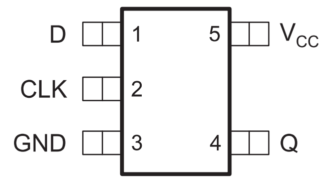


DCK Package
5-Pin SC70
Top View

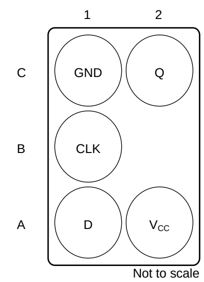


See mechanical drawings for dimensions.

DRL Package
5-Pin SOT
Top View



YZP Package
5-Pin DSBGA
Bottom View



Pin Functions

PIN			I/O	DESCRIPTION
NAME	DBV, DCK, DRL	YZP		
D	1	A1	I	Data input
CLK	2	B1	I	Positive-Edge-Triggered Clock input
GND	3	C1	—	Ground
Q	4	C2	O	Non-inverted output
V_{CC}	5	A2	—	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2)(3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
I_{OK}	Output clamp current	$V_O < 0$		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature		–65	150	°C
T_J	Junction temperature			150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		Machine Model (MM), A115-A	200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)[1]

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
		V_{CC} = 4.5 V to 5.5 V		0.3 × V_{CC}	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.4 Thermal Information

THERMAL METRIC[1]		SN74LVC1G79				UNIT
		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	YZP (DSBGA)	
		5 PINS	5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	247.2	277.6	294.3	144.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	154.5	179.5	129.9	1.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	86.8	75.9	143.4	39.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	58.0	49.7	14.3	0.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	86.4	75.1	144.0	39.7	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = –40°C to +85°C			T_A = –40°C to +125°C			UNIT
				MIN	TYP (1)	MAX	MIN	TYP (1)	MAX	
V_{OH}		I_{OH} = –100 µA	1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
		I_{OH} = –4 mA	1.65 V	1.2			1.2			
		I_{OH} = –8 mA	2.3 V	1.9			1.9			
		I_{OH} = –16 mA	3 V	2.4			2.4			
		I_{OH} = –24 mA		2.3			2.3			
		I_{OH} = –32 mA	4.5 V	3.8			3.8			
V_{OL}		I_{OL} = 100 µA	1.65 V to 5.5 V			0.1			0.1	V
		I_{OL} = 4 mA	1.65 V			0.45			0.45	
		I_{OL} = 8 mA	2.3 V			0.3			0.3	
		I_{OL} = 16 mA	3 V			0.4			0.4	
		I_{OL} = 24 mA				0.55			0.55	
		I_{OL} = 32 mA	4.5 V			0.55			0.55	
I_I	All inputs	V_I = 5.5 V or GND	0 to 5.5 V			±10			±5	µA
I_{off}		V_I or V_O = 5.5 V	0			±10			±10	µA
I_{CC}		V_I = 5.5 V or GND, I_O = 0	1.65 V to 5.5 V			10			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	µA
C_i		V_I = V_{CC} or GND	3.3 V		4			4		pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Timing Requirements: T_A = –40°C to +85°C

over operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER			T_A = –40°C to +85°C								UNIT
			V_{CC} = 1.8 ± 0.15 V		V_{CC} = 2.5 ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			160		160		160		160	MHz
t_w	Pulse duration, CLK high or low		2.5		2.5		2.5		2.5		ns
t_{su}	Setup time before CLK↑	Data high	2.2		1.4		1.3		1.2		ns
		Data low	2.6		1.4		1.3		1.2		
t_h	Hold time, data after CLK↑		0.3		0.4		1		0.5		ns

6.7 Timing Requirements: T_A = –40°C to +125°C

over operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER			T_A = –40°C to +125°C								UNIT
			V_{CC} = 1.8 ± 0.15 V		V_{CC} = 2.5 ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			160		160		160		160	MHz
t_w	Pulse duration, CLK high or low		2.5		2.5		2.5		2.5		ns
t_{su}	Setup time before CLK↑	Data high	2.2		1.4		1.3		1.2		ns
		Data low	2.6		1.4		1.3		1.2		
t_h	Hold time, data after CLK↑		0.3		0.4		1		0.5		ns

6.8 Switching Characteristics: C_L = 15 pF, T_A = –40°C to +85°C

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = –40°C to +85°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			160		160		160		160		MHz
t_{pd}	CLK	Q	2.5	9.1	1.2	6	1	4	0.8	3.8	ns

6.9 Switching Characteristics: C_L = 30 or 50 pF, T_A = –40°C to +85°C

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = –40°C to +85°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			160		160		160		160		MHz
t_{pd}	CLK	Q	3.9	9.9	2	7	1.7	5	1	4.5	ns

6.10 Switching Characteristics: C_L = 30 pF or 50 pF, T_A = –40°C to +125°C

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = –40°C to +125°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			160		160		160		160		MHz
t_{pd}	CLK	Q	3.9	12	2	8.5	1.7	6	1	5	ns

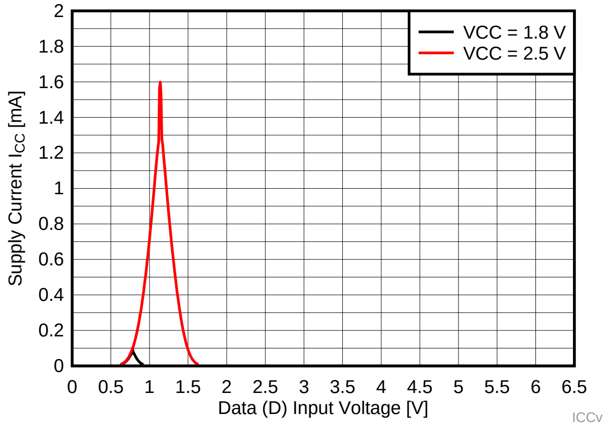
6.11 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	26	26	27	30	pF

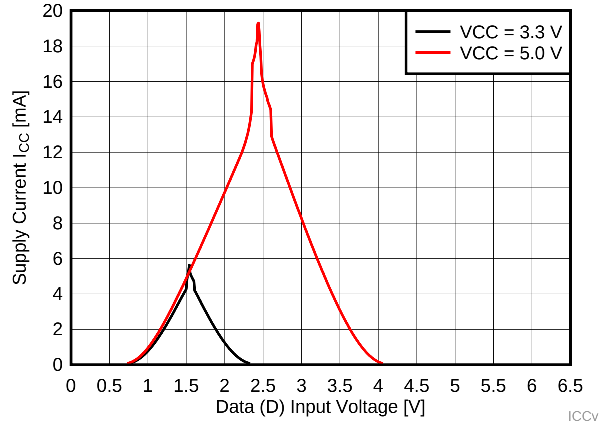
6.12 Typical Characteristics

This plot shows the different I_{CC} values for various voltages on the data input (D). Voltage sweep on the input is from 0 V to 6.5 V.



VCC = 1.8 V VCC = 2.5 V

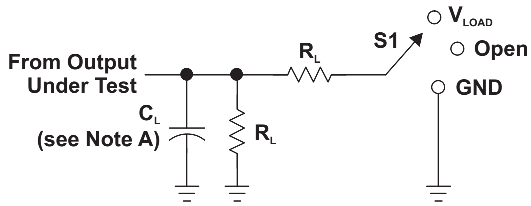
Figure 1. Supply Current (I_{CC}) vs Data (D) Input Voltage



VCC = 3.3 V VCC = 5 V

Figure 2. Supply Current (I_{CC}) vs Data (D) Input Voltage

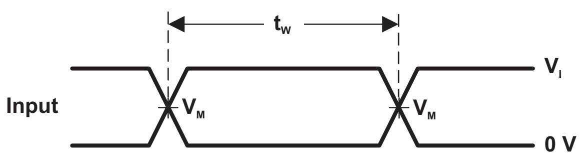
7 Parameter Measurement Information



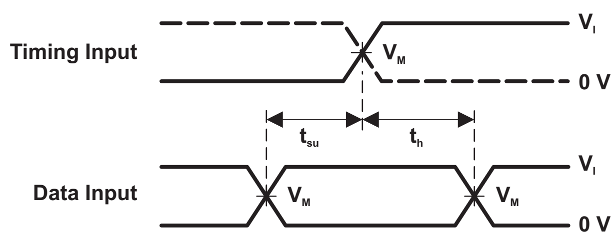
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

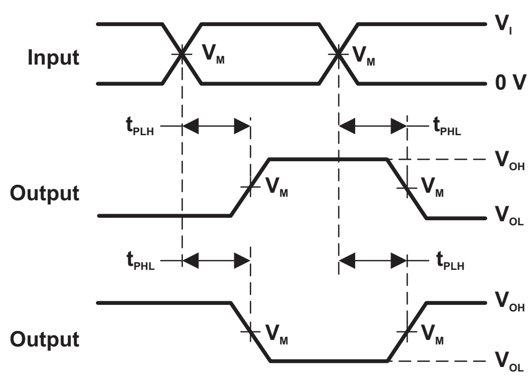
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 MΩ	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.3 V



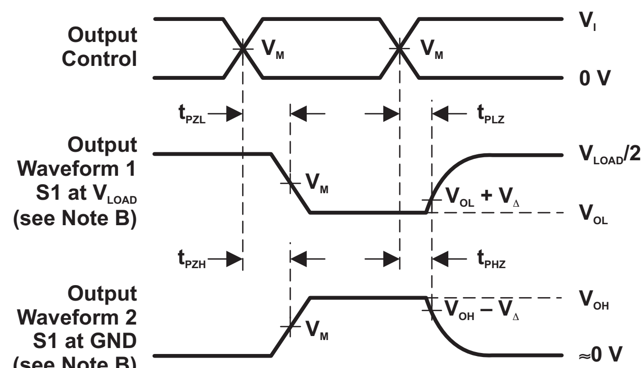
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

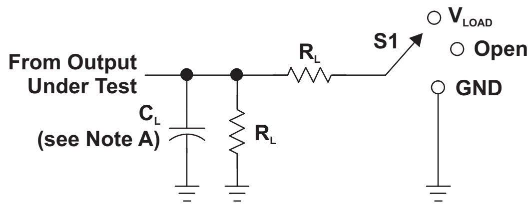


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

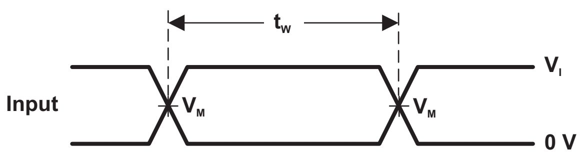
Parameter Measurement Information (continued)



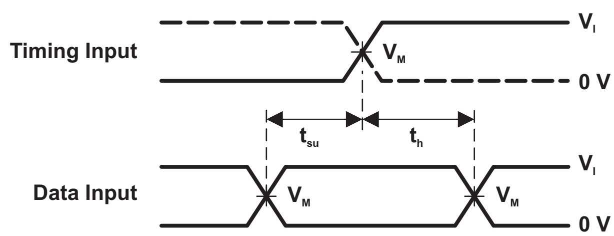
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

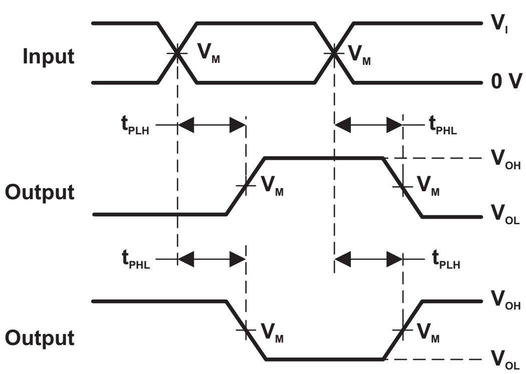
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



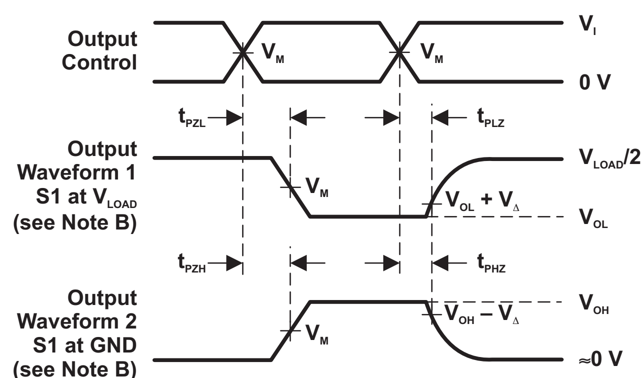
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC1G79 is a single positive-edge-triggered D-type flip-flop. Data at the input (D) is transferred to the output (Q) on the positive-going edge of the clock pulse when the setup time requirement is met. Because the clock triggering occurs at a voltage level, it is not directly related to the rise time of the clock pulse. This allows for data at the input to be changed without affecting the level at the output, following the hold-time interval.

8.2 Functional Block Diagram

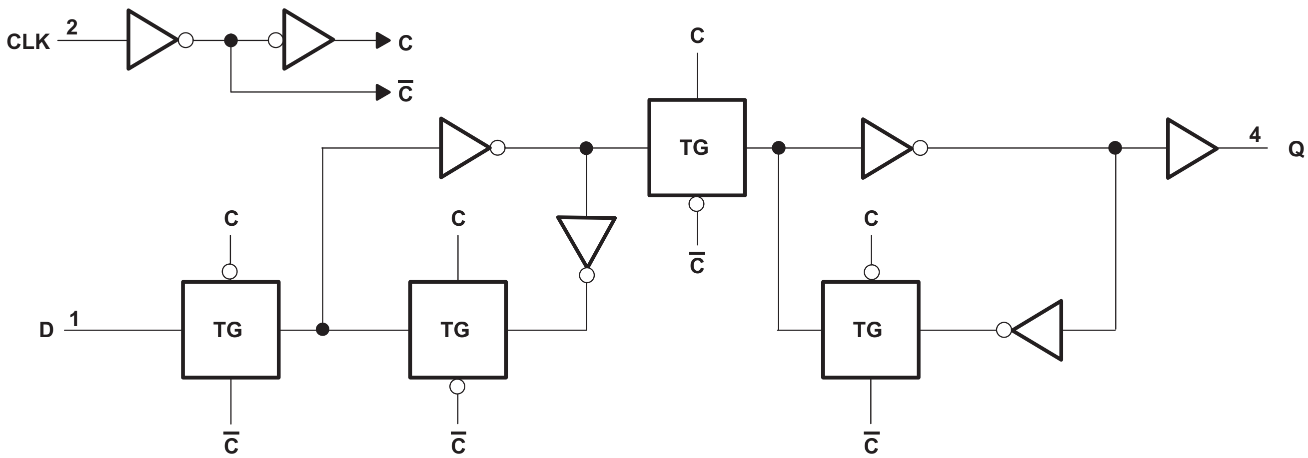


Figure 5. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *Absolute Maximum Ratings* must be followed at all times.

8.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Recommended Operating Conditions*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by Δt/Δv in *Recommended Operating Conditions* to avoid excessive currents and oscillations. If tolerance to a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

Feature Description (continued)

8.3.3 Clamp Diodes

The inputs and outputs to this device have negative clamping diodes.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

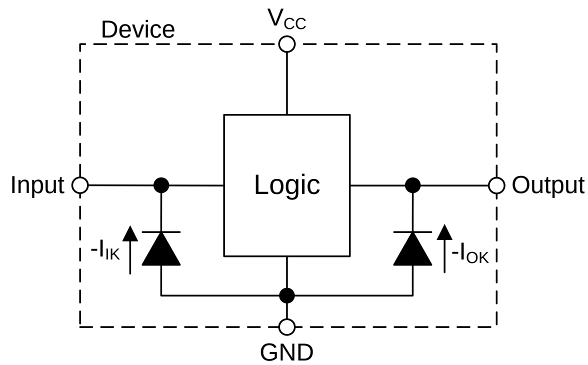


Figure 6. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.4 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high impedance state when the supply voltage is 0 V. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

8.3.5 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Absolute Maximum Ratings*.

8.4 Device Functional Modes

Table 1 lists the functional modes of SN74LVC1G79.

Table 1. Function Table

INPUTS		OUTPUT
CLK	D	Y
↑	H	H
↑	L	L
L	X	Q_0

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

A useful application for the SN74LVC1G79 is using it as a data latch with low-voltage data retention. This application implements the use of a microcontroller GPIO pin to act as a clock to set the output state and a second GPIO to provide the input data. If the SN74LVC1G79 is being powered from 1.8 V and there is concern that a power glitch could exist as low as 1.5 V, the device will retain the state of the Q output. An example of this data retention is shown in Figure 8 where the V_{CC} drops to 1.5 V and the Q output maintains the HIGH output state when V_{CC} returns to 1.8 V. If the V_{CC} voltage drops below 1.5 V, data retention is not guaranteed.

9.2 Typical Application

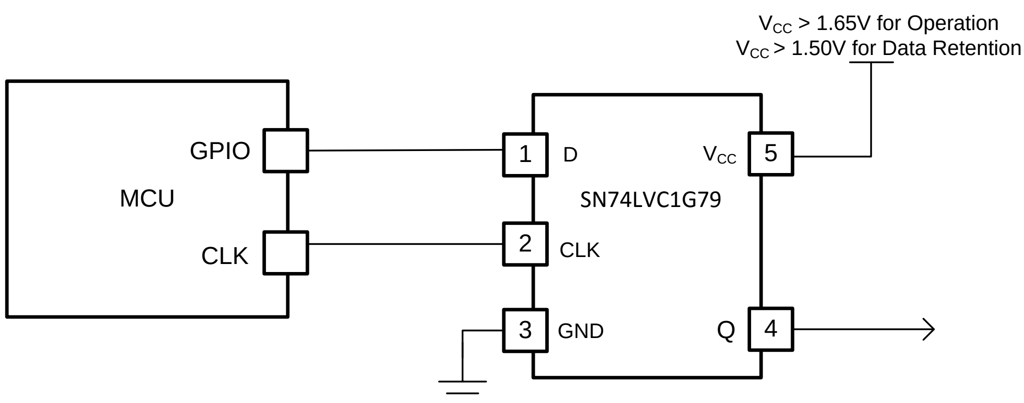


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Figure 7. Low Voltage Data Retention With SN74LVC1G79

9.2.1 Design Requirements

The SN74LVC1G79 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits.

9.2.2 Detailed Design Procedure

1. Recommended input conditions:
   – For rise time and fall time specifications, see Δt/Δv in *Recommended Operating Conditions*.
   – For specified high and low levels, see V_{IH} and V_{IL} in *Recommended Operating Conditions*.
   – Input voltages are recommended to not go below 0 V and not exceed 5.5 V for any V_{CC}. See *Recommended Operating Conditions*.
2. Recommended output conditions:
   – Load currents should not exceed ±50 mA. See *Absolute Maximum Ratings*.
   – Output voltages are recommended to not go below 0 V and not exceed the V_{CC} voltage. See *Recommended Operating Conditions*.

Typical Application (continued)

9.2.3 Application Curve

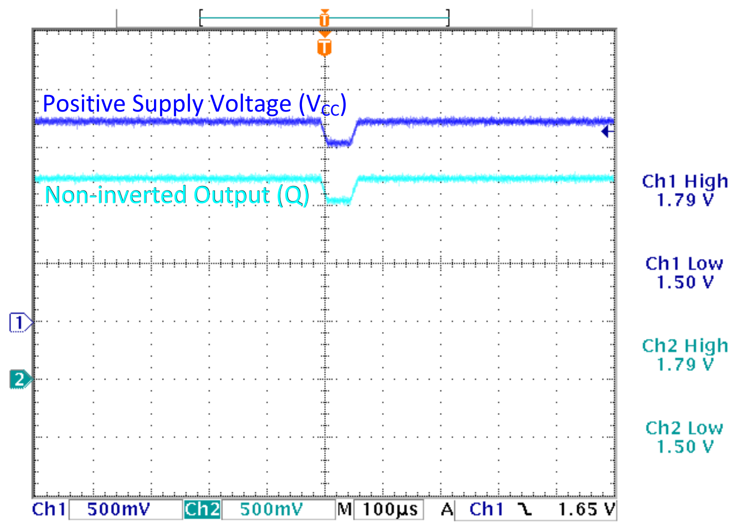

Figure 8. Data Retention With V_{CC} Glitch Down to 1.5 V

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in *Recommended Operating Conditions*. A 0.1-µF bypass capacitor is recommended to be connected from the VCC terminal to GND to prevent power disturbance. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 µF and 1 µF are commonly used in parallel. The bypass capacitor must be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 9 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

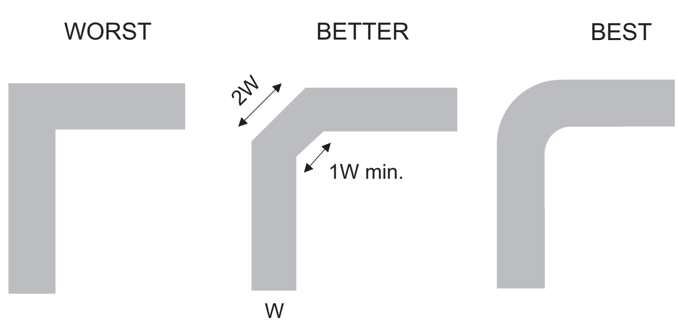

Figure 9. Trace Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- *Implications of Slow or Floating CMOS Inputs*, SCBA004
- *Understanding and Interpreting Standard Logic Data Sheets*, SZZA036
- *Power-Up Behavior of Clocked Devices*, SCHA005

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G79DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C795, C79F, C79J, C79R)	Samples
SN74LVC1G79DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C795, C79F, C79J, C79R)	Samples
SN74LVC1G79DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C79F	Samples
SN74LVC1G79DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(CR5, CRF, CRJ, CR R)	Samples
SN74LVC1G79DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CR5	Samples
SN74LVC1G79DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(CR5, CRF, CRJ, CR R)	Samples
SN74LVC1G79DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CR5	Samples
SN74LVC1G79DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CR7, CRR)	Samples
SN74LVC1G79YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(CR7, CRN)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

[(5)] Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

[(6)] Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G79 :

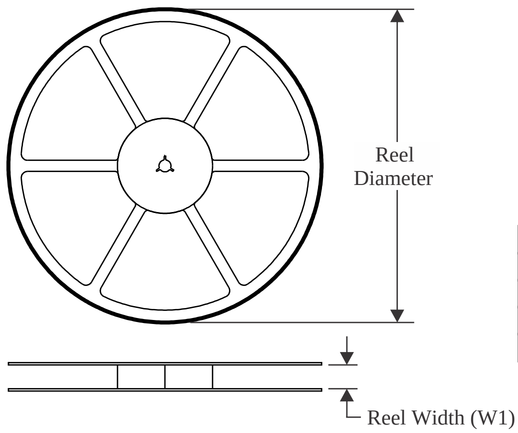
- Automotive : SN74LVC1G79-Q1
- Enhanced Product : SN74LVC1G79-EP

NOTE: Qualified Version Definitions:

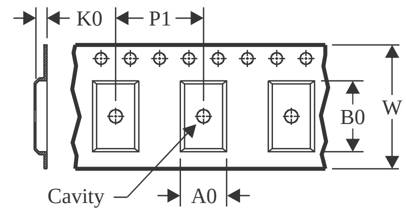
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

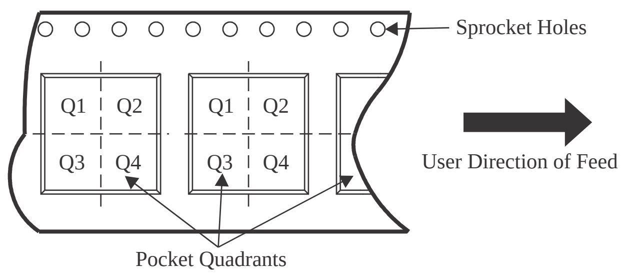


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

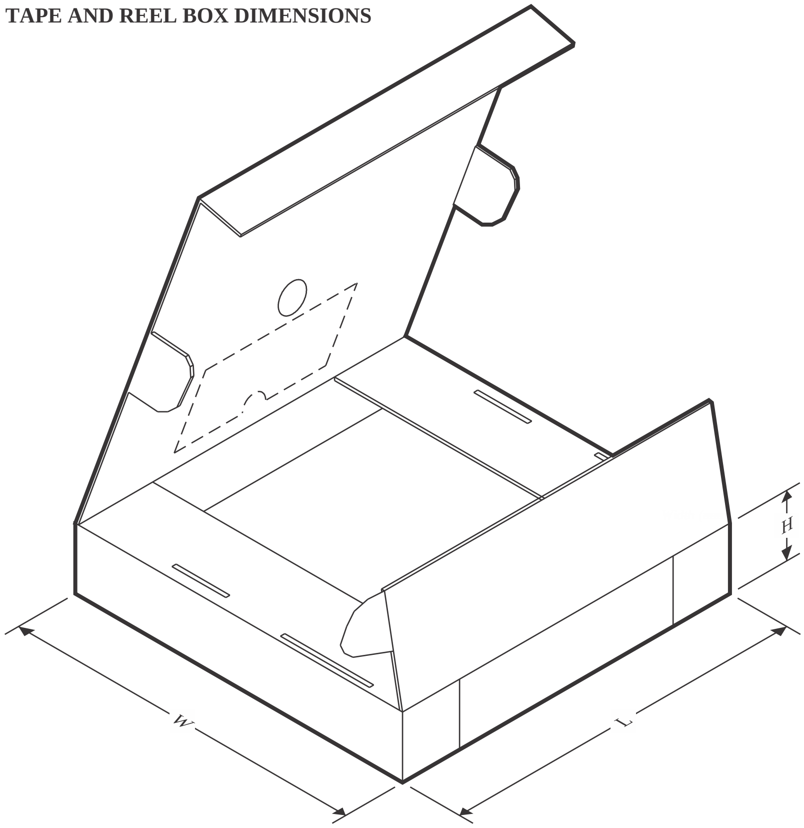
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

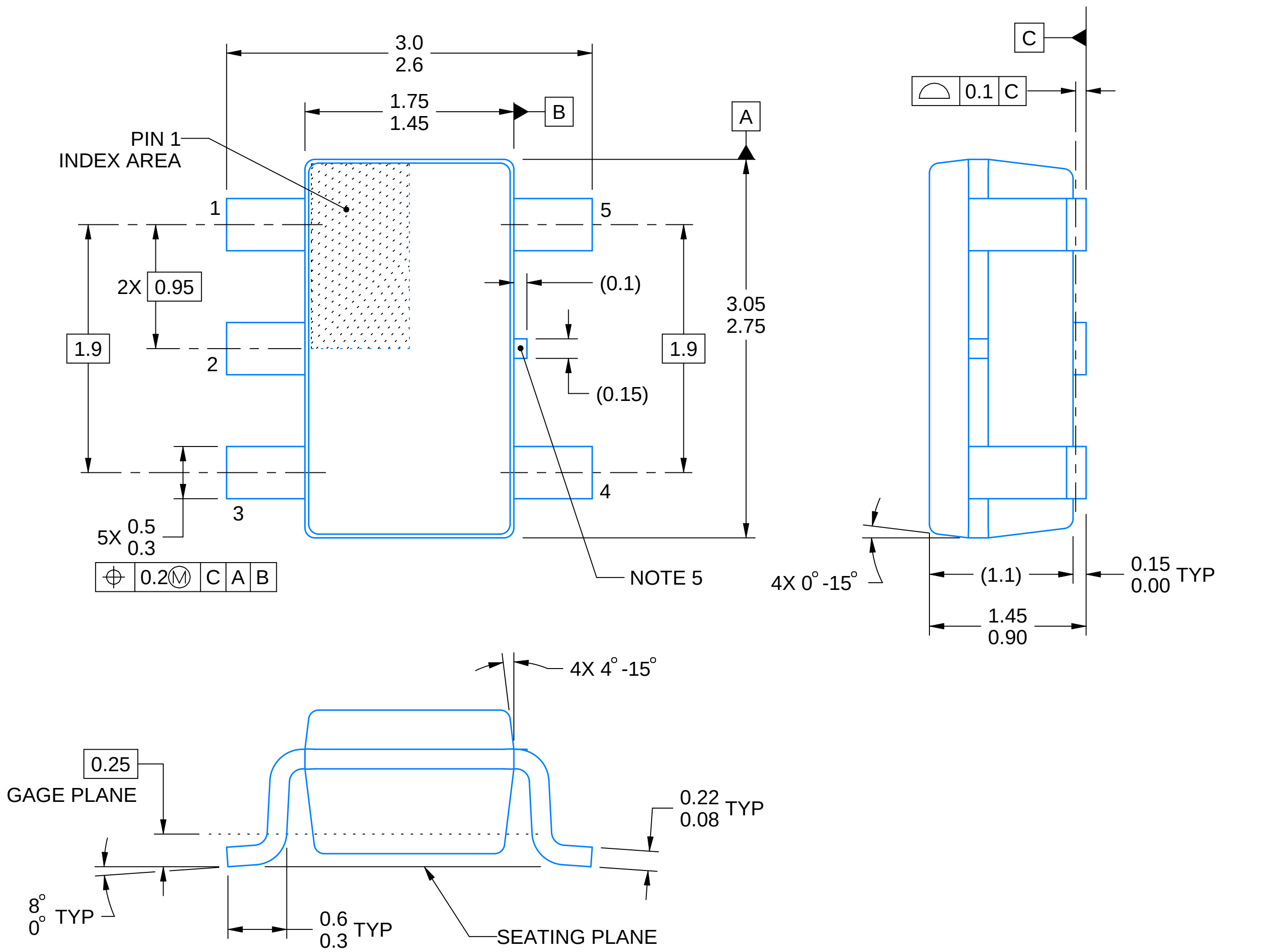
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G79DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G79DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G79DBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G79DBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G79DBVTG4	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G79DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G79DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G79DCKT	SC70	DCK	5	250	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G79DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G79DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G79YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

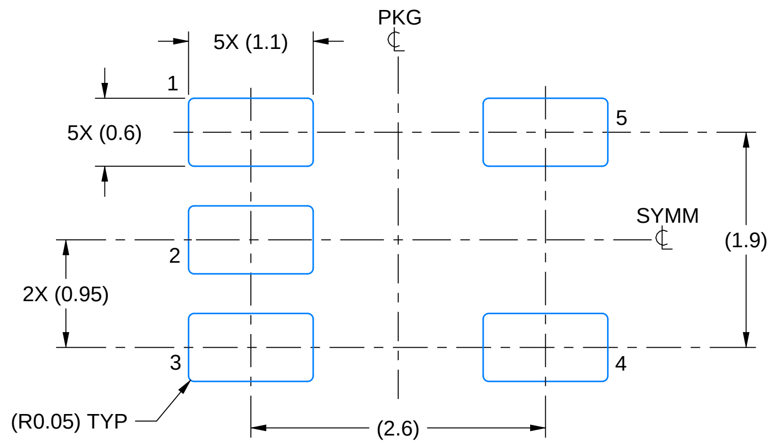
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G79DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G79DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G79DBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
SN74LVC1G79DBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
SN74LVC1G79DBVTG4	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G79DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74LVC1G79DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G79DCKT	SC70	DCK	5	250	210.0	185.0	35.0
SN74LVC1G79DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G79DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G79YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0



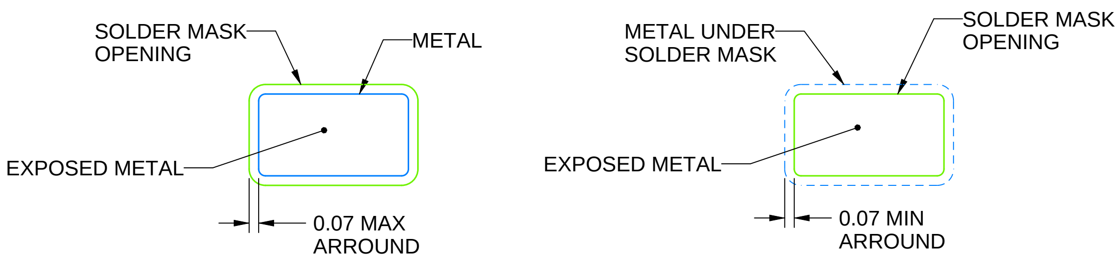
4214839/K 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



NON SOLDER MASK
DEFINED
(PREFERRED)

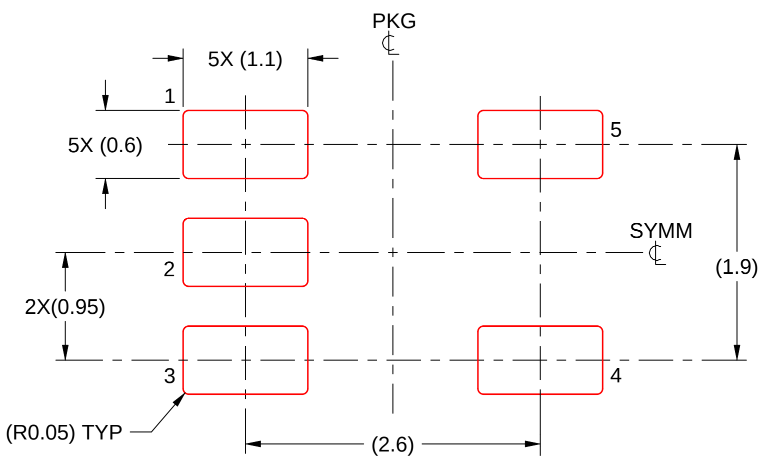
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

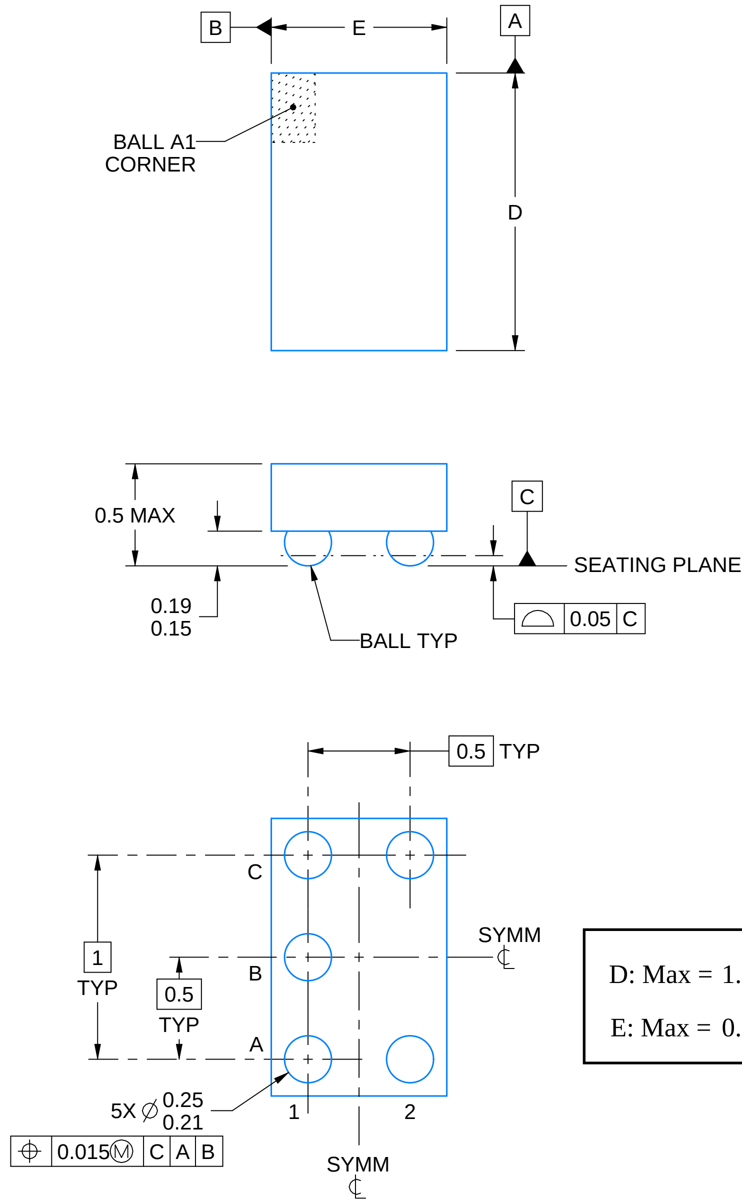


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



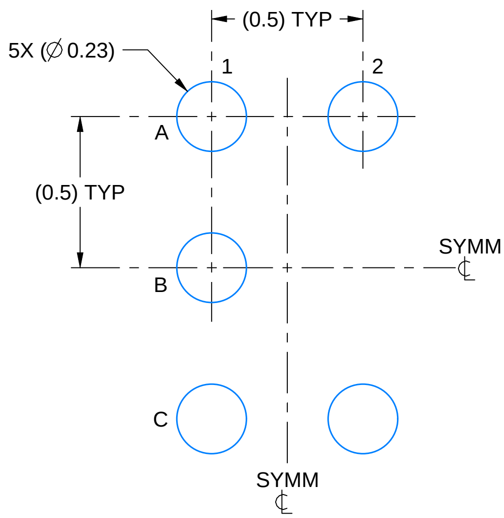
D: Max = 1.418 mm, Min =1.358 mm

E: Max = 0.918 mm, Min =0.858 mm

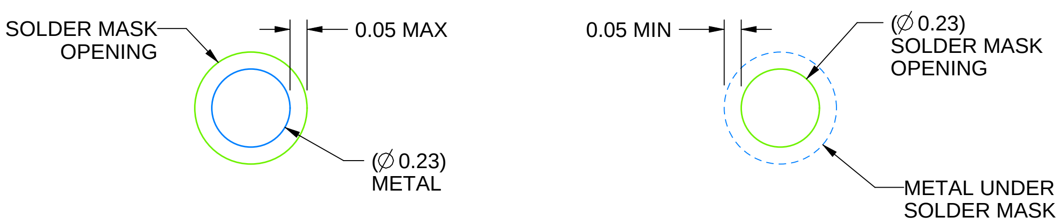
4219492/A 05/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X



NON-SOLDER MASK DEFINED (PREFERRED)

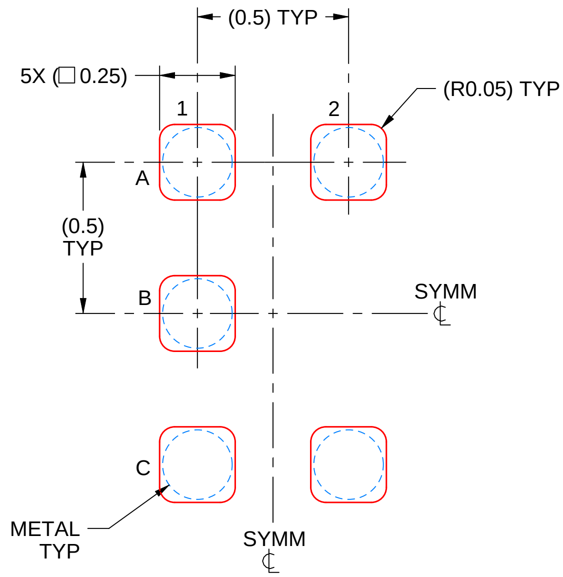
SOLDER MASK DEFINED

SOLDER MASK DETAILS
NOT TO SCALE

4219492/A 05/2017

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

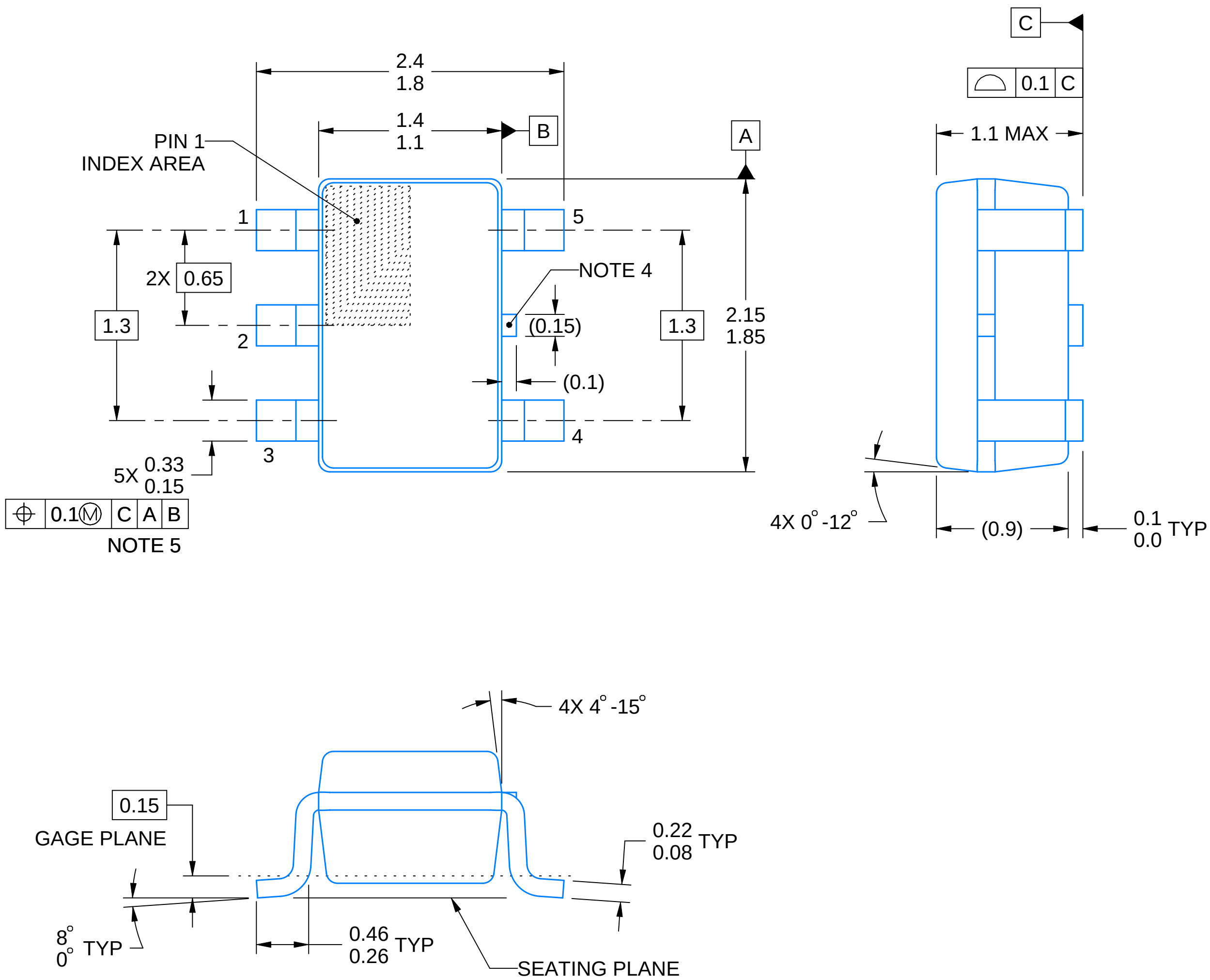


SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4219492/A 05/2017

NOTES: (continued)

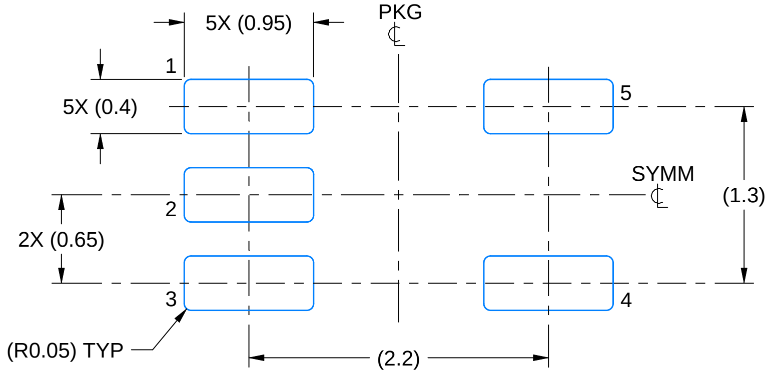
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



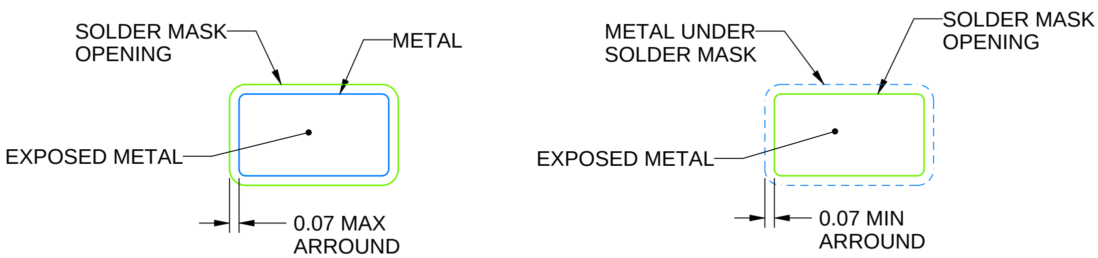
4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



NON SOLDER MASK
DEFINED
(PREFERRED)

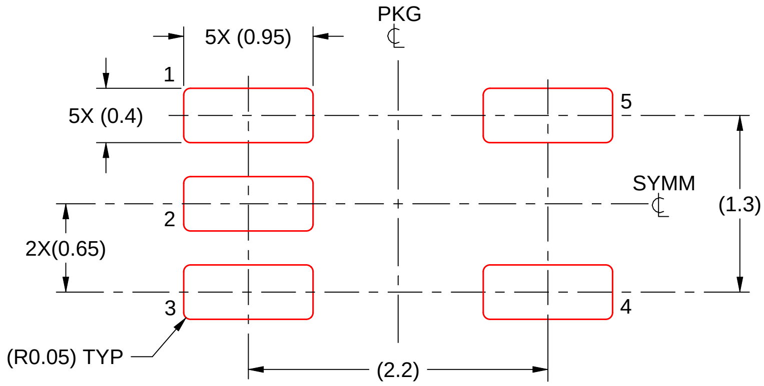
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

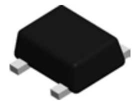


SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

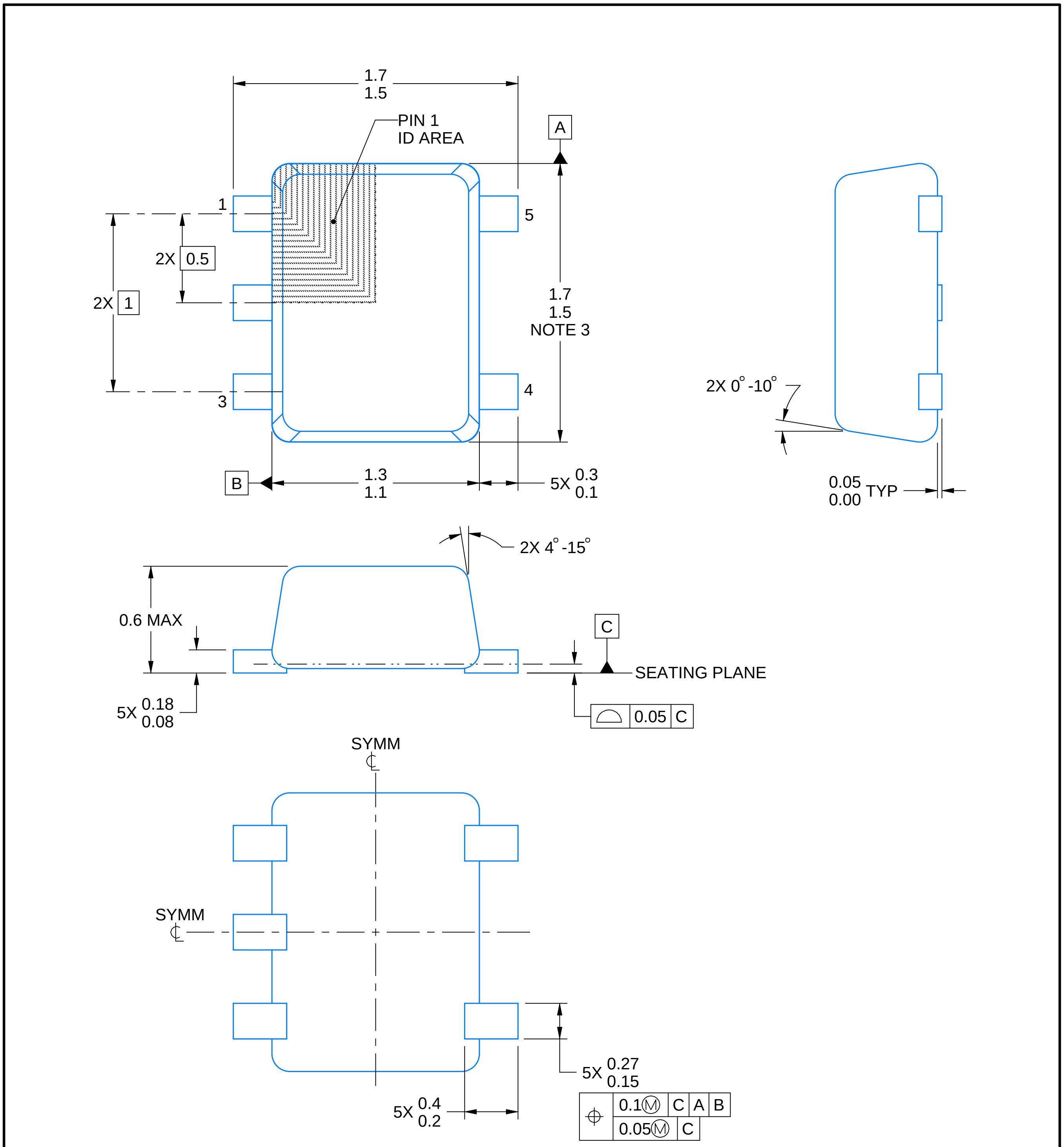
4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.



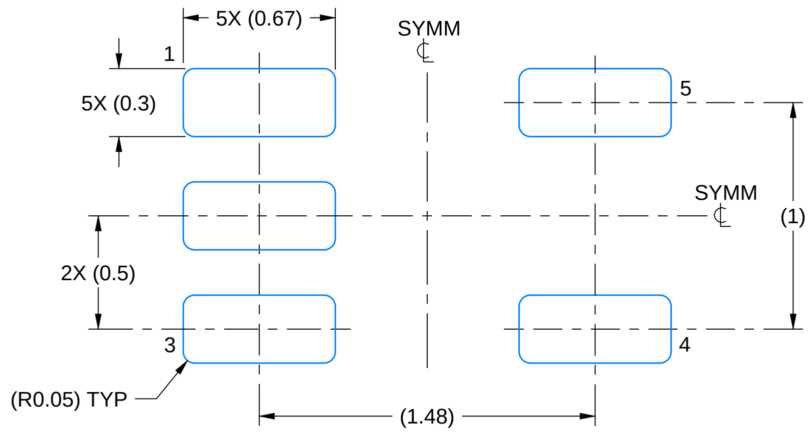
PLASTIC SMALL OUTLINE



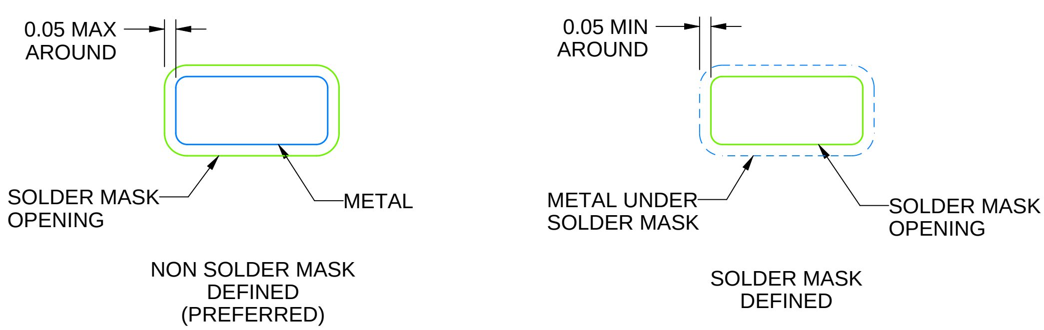
4220753/E 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD-1



LAND PATTERN EXAMPLE
SCALE:30X

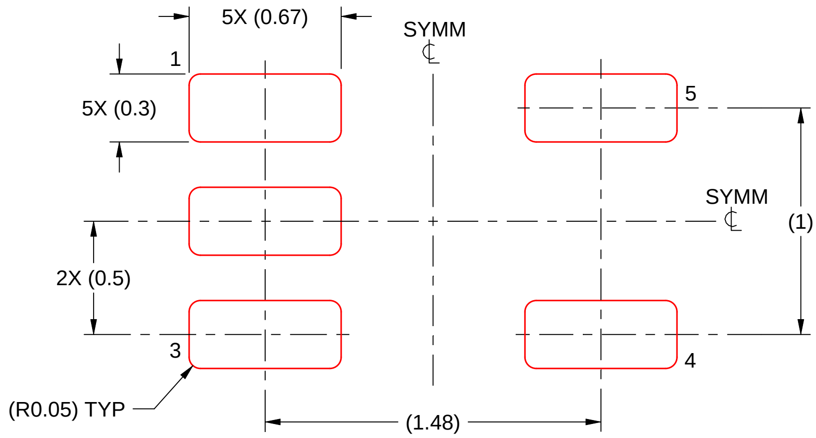


SOLDERMASK DETAILS

4220753/E 11/2024

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

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NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.